RENESAS HD74LVCZ16240A

16-bit Buffers / Line Drivers with 3-state Outputs

REJ03D0373–0200 (Previous ADE-205-231 (Z)) Rev.2.00 Aug. 19, 2004

Description

The HD74LVCZ16240A has sixteen inverter drivers with three state outputs in a 48 pin package. This device is a inverting buffer and has four active low enables ($1\overline{G}$ to $4\overline{G}$). Each enable independently controls four buffers.

When V_{CC} is between 0 and 1.5 V, the device is in the high impedance state during power up or power down.

Low voltage and high-speed operation is suitable at battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{CC} = 2.7$ to 5.5 V
- All inputs V_{IH} (Max) = 5.5 V (@V_{CC} = 0 to 5.5 V)
- All outputs V_0 (Max) = 5.5 V (@V_{CC} = 0 V or output off state)
- Typical V_{OL} ground bounce < 0.8 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@V_{CC} = 3.3 V, Ta = 25°C)
- High impedance state during power up and power down
- Power off disables outputs, permitting live insertion
- High output current ± 24 mA (@V_{CC} = 3.0 to 5.5 V)
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LVCZ16240ATEL	TSSOP-48 pin	TTP-48DBV	Т	EL (1,000 pcs/reel)

Function Table

Inputs Output Y G A Output Y H X Z L H L L L H

H: High level

L: Low level

X: Immaterial

Z: High impedance



Pin Arrangement

1 <u>G</u> 1	48	2 G
1Y1 2	47]1A1
1Y2 3	46	1A2
GND 4	45	GND
1Y3 5	44	1A3
1Y4 6	43	1A4
V _{CC} 7	42	Vcc
2Y1 8	41	2A1
2Y2 9	40	2A2
GND 10	39	GND
2Y3 11	38	2A3
2Y4 12	37	2A4
3Y1 13	36	3A1
3Y2 14	35	3A2
GND 15		GND
3Y3 16	33	3A3
3Y4 17		3A4
V _{CC} 18		Vcc
4Y1 19	30	4A1
4Y2 20		4A2
GND 21	28	GND
4Y3 22	27	4A3
4Y4 23		4A4
4 <u>G</u> 24	25	3 G
	(Top view)	



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	–0.5 to 7.0	V	
Input voltage	VI	–0.5 to 7.0	V	
Output voltage	Vo	–0.5 to 7.0	V	Output "Z" or V _{CC} : OFF
		–0.5 to V _{CC} +0.5		Output "H" or "L"
Input diode current	I _{IK}	-50	mA	V ₁ < 0
Output diode current	I _{OK}	-50	mA	V ₀ < 0
Output current	Ιo	±50	mA	
V _{CC} , GND current	I _{CC} or I _{GND}	±100	mA	
Storage temperature	Tstg	-65 to 150	°C	

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

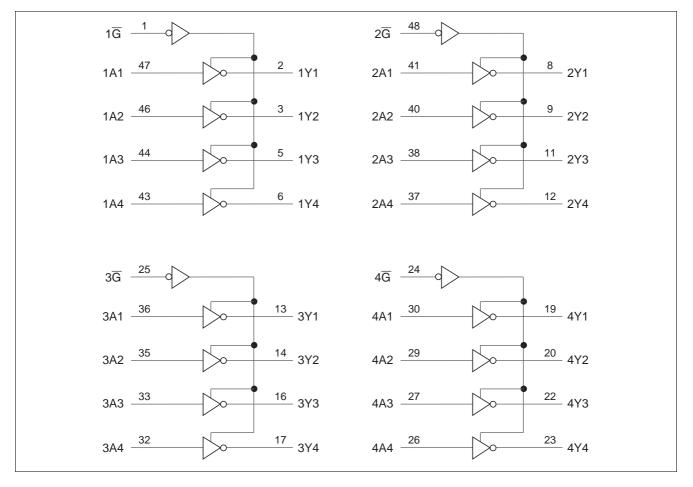
Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	Vcc	2.7 to 5.5	V	At operation
Input voltage	VI	0 to 5.5	V	
Output voltage	Vo	0 to 5.5	V	Output "Z" or V _{CC} : OFF
		0 to V _{CC}		Output "H" or "L"
Output current	I _{OH}	-12	mA	V _{CC} = 2.7 V
		-24 ^{*1}		$V_{CC} = 3.0$ to 5.5 V
	IOL	12	mA	V _{CC} = 2.7 V
		24 ^{*1}		V_{CC} = 3.0 to 5.5 V
Input rise / fall time	t _r , t _f	0 to 6	ns / V	
Operating temperature	Та	-40 to +85	°C	
	Id	-40 10 +65	U	

Note: 1. Duty cycle $\leq 50\%$



Logic Diagram





Electrical Characteristics

							$(Ta = -40 \text{ to } 85^{\circ}\text{C})$
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Input voltage	VIH	2.7 to 3.6	2.0		_	V	
		4.5 to 5.5	V _{CC} ×0.7	_	_		
	VIL	2.7 to 3.6		_	0.8	V	
		4.5 to 5.5	_	—	V _{CC} ×0.3		
Output voltage	V _{OH}	2.7 to 5.5	V _{CC} -0.2	—	—	V	I _{OH} = -100 μA
		2.7	2.2	—	—		I _{OH} = -12 mA
		3.0	2.4	—	—		
		3.0	2.2	_	_		$I_{OH} = -24 \text{ mA}$
		4.5	3.8	_	_		
	V _{OL}	2.7 to 5.5		_	0.2	V	I _{OL} = 100 μA
		2.7	_	_	0.4		I _{OL} = 12 mA
		3.0	_	_	0.55		I _{OL} = 24 mA
		4.5		_	0.55		
Input current	I _{IN}	0 to 5.5	_	—	±5	μΑ	$V_{IN} = 0$ to 5.5 V
Off state output	l _{oz}	2.7 to 5.5	—	—	±5	μA	$V_{OUT} = 0$ to 5.5 V
current	IOZPU	0 to 1.5	_	_	±5		$V_{OUT} = 0.5 \text{ to } 5.5 \text{ V},$
	IOZPD	1.5 to 0	_	_	±5		Output enable = don't care
Output leak current	I _{OFF}	0	_	_	±5	μA	V_{IN} or $V_O = 5.5 V$
Quiescent supply	Icc	2.7 to 3.6	_	_	225	μA	$V_{IN} = 3.6$ to 5.5 V ^{*1} , $I_0 = 0$
current		2.7 to 5.5	_	_	350	_	$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	2.7 to 3.6	_	_	500	μA	V_{IN} = one input at (V _{CC} -0.6) V,
							other inputs at V_{CC} or GND
Input capacitance	CIN	3.3	_	4.1	—	pF	$V_{IN} = V_{CC}$ or GND
Output capacitance	Co	3.3	_	8.1	_	pF	$V_{OUT} = V_{CC} \text{ or } GND$

Note: 1. This applies in the disabled state only.

Switching Characteristics

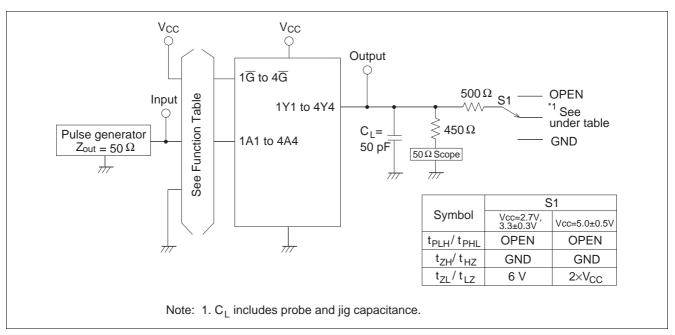
							$(Ta = -40 \text{ to } 85^{\circ}C)$	
ltem	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH}	2.7		_	5.3	ns	А	Y
	t _{PHL}	3.3±0.3	1.1	_	4.7			
		5.0±0.5			4.2			
Output enable time	t _{zH}	2.7		_	6.2	ns	G	Y
	t _{ZL}	3.3±0.3	1.0	_	5.0			
		5.0±0.5	_	_	4.5			
Output disable time	t _{HZ}	2.7		_	7.4	ns	G	Y
	t _{LZ}	3.3±0.3	1.8	_	6.3			
		5.0±0.5			4.7			
Between output pin skew *1	t _{OSLH}	2.7		_	_	ns		
	toshl	3.3±0.3		_	1.0			
		5.0±0.5		_	1.0			

Note: 1. This parameter is characterized but not tested.

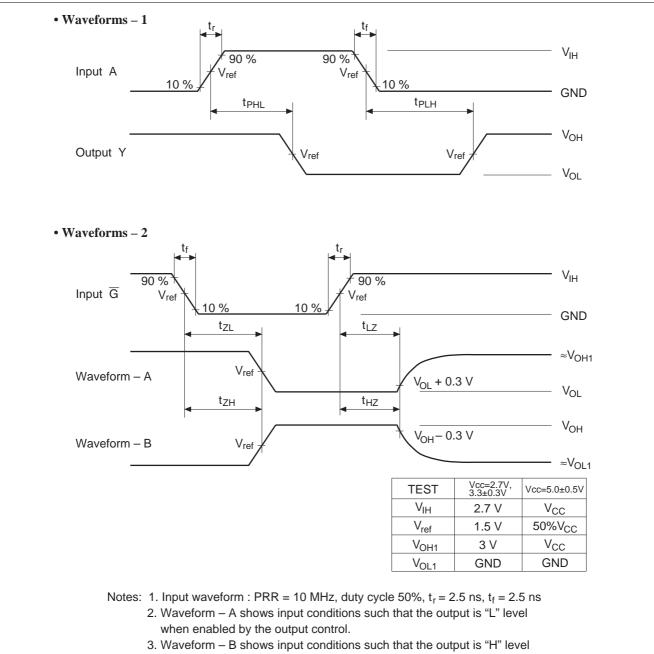
 $t_{\text{OSLH}} = |t_{\text{PLHm}} - t_{\text{PLHn}}|, \ t_{\text{OSHL}} = |t_{\text{PHLm}} - t_{\text{PHLn}}|$



Test Circuit



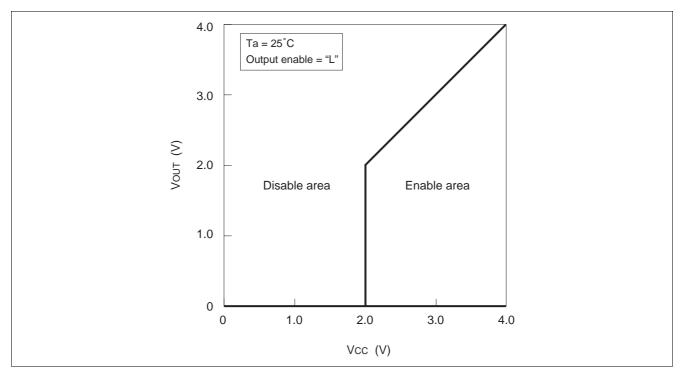




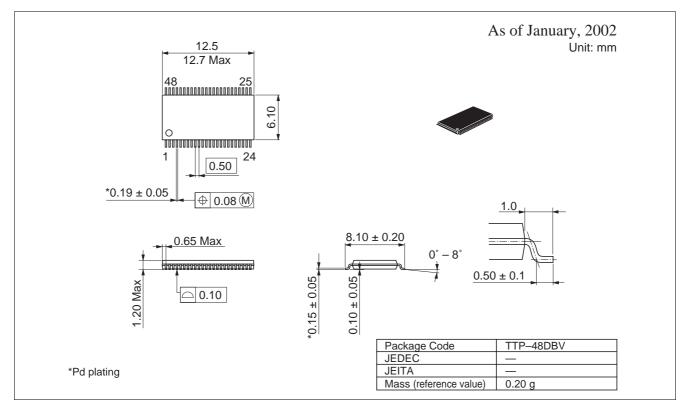
when enabled by the output control.



Power up / down Characteristics



Package Dimensions



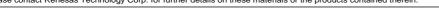


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